

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	102	(gate with ((two dual double twin) near charge near (storage\$1 trap\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/05 06:55
L2	5	memory AND substrate AND well\$1 AND (gate ADJ (insulat\$3 oxide dielectric)) AND (gate ADJ electrode) AND ((two dual twin double) NEAR charg\$3 NEAR (storag\$3 trap\$4)) AND (sidewall (side NEAR wall\$1)) AND channel AND ((diffus\$3 dop\$4 implant\$5) NEAR (area\$1 region\$1)) AND current AND (voltage potential) AND (hole\$1 electron\$1).CLM.	US-PGPUB; USPAT	OR	ON	2005/10/05 07:04
S1	6	((("4881108") or ("6434053") or ("6348711"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/06/22 19:33
S2	6	("5999444"   "6011725"   "6081456"   "6137718"   "6147904"   "6163048").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/18 11:48
S3	43	("4173766"   "4173791"   "4360900"   "4380057"   "4527257"   "4586163"   "4630085"   "4667217"   "4742491"   "4847808"   "4870470"   "5021999"   "5159570"   "5168334"   "5172338"   "5214303"   "5293563"   "5295108"   "5305262"   "5311049"   "5345425"   "5349221"   "5359554"   "5394355"   "5412601"   "5414693"   "5418743"   "5424978"   "5426605"   "5434825"   "5440505"   "5450341"   "5450354"   "5477499"   "5592417"   "5606523"   "5654568"   "5754475"   "5768192"   "5793079"   "5812449"   "5825686"   "5841700").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/18 12:26
S4	2	("6011725").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/06/18 12:27
S5	4	((("6627498") or ("6335554"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/06/20 10:06
S6	10	("4881108"   "5408115"   "5422504"   "5424979"   "5768192"   "5780341"   "5969383"   "6030869"   "6040995"   "6093605").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/20 10:08

S7	7	("5408115"   "5614747"   "5691937"   "5703388"   "5729035"   "5780891"   "5796139").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/20 10:14
S8	10	("5120672"   "5324675"   "5496753"   "5830771"   "5989957"   "6238978"   "6255165"   "6410957"   "6440789"   "6486030").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/20 10:18
S9	0	voltage near less near than near reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:10
S10	0	(potential voltage) near less near than near reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:36
S11	217583	reference near (potential voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:36
S12	0	(potential voltage) near less near than near reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:36
S13	225	(substrate (well near region)) near reference near (potential voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:37
S14	89	S13 and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:50
S15	14	memory with (substrate (well near region)) near reference near (potential voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:42
S16	2069	memory with (substrate (well near region)) near (potential voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:53

S17	1681366	memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:50
S18	74634	writ\$3 near operat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:52
S19	60965	S18 and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:52
S20	209	memory with ((substrate (well near region)) near (potential voltage)) with (source near (potential voltage))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:54
S21	107	S20 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:15
S22	10	("4881108"   "5408115"   "5422504"   "5424979"   "5768192"   "5780341"   "5969383"   "6030869"   "6040995"   "6093605").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/04 19:07
S23	8399	257/239,261,298,314-326,E27.078,E29. 3-E29.309.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:12
S24	5594	438/201,211,216,241,257,258,260-266,591, 593.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:13
S25	12633	S23 or S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:13

S26	1	S25 and ((gate near electrode) with ((two dual double twin) near charge near (storage\$1 trap\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:26
S27	8	((gate near electrode) with ((two dual double twin) near charge near (storage\$1 trap\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:17
S28	43	S25 and (gate with ((two dual double twin) near charge near (storage\$1 trap\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:27